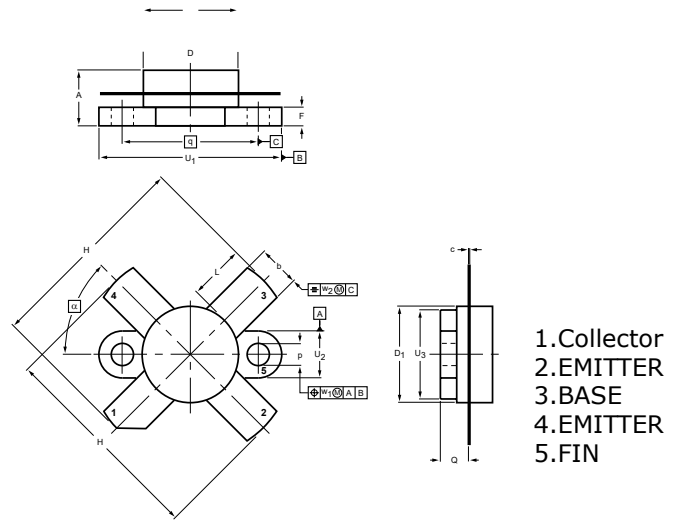


DESCRIPTION

Designed primarily for applications as high-power linear power amplifier from 2.0 to 30MHz

FEATURES

- Specified 28V, 30MHz Characteristic
- $P_o = 150W$ PEP
- $G_p = 13$ Typ. min. at 150 W/30MHz
- IMD3 = -30 dBc max. at 150 W(PEP)
- Omnigold™ Metalization System



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V _{CB0}	85	V
Collector-Emitter Voltage	V _{CES}	85	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	3	V
Collector Current	I _C	20	A
Collector Power Dissipation	P _{DISS}	290	W
Junction Temperature	T _J	-65 to 150	°C
Storage Temperature Range	T _{STG}	-65 to 150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =200mA, I _B =0	35	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	I _C =100mA, V _{EB} =0	85	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	3	-	-	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =5A	15	30	120	
Collector Output Capacitance	C _{ob}	V _{CB} =12.5V, I _E =0 f=1MHz	-	420	-	pF
Power Gain	G _p	V _{CC} =28V, P _{OUT} =150W I _{CQ} =100mA, f=30MHz	10	13	-	dB
Collector Efficiency	η _c		-	45	-	%
Intermodulation Distortion	IMD3		-	-33	-30	dBc
Series Equivalent Input Impedance	Z _{IN}	V _{CC} =28V P _{OUT} =150W f=30MHz	-	0.75 - j0.24	-	Ω

Note : Above parameters , ratings , limits and conditions are subject to change.